Abstracts

Picosecond Optoelectronic Characterization of a Heterojunction Bipolar Transistor

M. Matloubian, H. Fetterman, M. Kim, A. Oki, J. Camou, S. Moss, D. Smith and J. Knudsen. "Picosecond Optoelectronic Characterization of a Heterojunction Bipolar Transistor." 1989 MTT-S International Microwave Symposium Digest 89.3 (1989 Vol. III [MWSYM]): 889-892.

A time domain network analyzer with a bandwidth greater than 100 GHz was constructed using picosecond optoelectronic techniques. The S-parameters of a heterojunction bipolar transistor with an f/sub max/ of 35 GHz was measured using this system. The measured S-parameters agree with those obtained using a conventional automatic network analyzer over the range of frequency overlap.

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